

**AMENDMENTS TO THE CLAIMS**

Please cancel claim 2 without prejudice or disclaimer to the subject matter therein.

Please amend claims 1, 3 - 6, and 9 - 17 as follows.

1. **(Currently Amended)** A two-dimensional patterning method[[,]] comprising:  
implanting gas ions on a substrate in a desired pattern to form a blister having a dome-shaped swelling in a specified depth range in the substrate; and wherein a two-dimensional pattern is formed by  
destroying [[a]] the blister disposed on a substrate by electron irradiation or ion  
irradiation to form a two-dimensional pattern with a specified depth.

2. **(Canceled)**

3. **(Currently Amended) [[A]]** The two-dimensional patterning method according to  
claim 1, further comprising:  
after forming the blister,  
wherein a two-dimensional pattern of a uncoated clean surface is formed by forming a  
film on [[a]] the blister, disposed on a substrate and  
destroying and removing the blister together with the formed film by electron irradiation  
or ion irradiation to form a two-dimensional pattern of an uncoated clean surface.

4. (Currently Amended) [[A]] The two-dimensional patterning method according to claim 1, further comprising:

after forming the blister,

~~wherein a two-dimensional pattern of a non-reacted clean surface is formed by executing surface reaction on [[a]] the blister disposed on a substrate to form a reacted film, and destroying and removing the blister together with the reacted film by electron irradiation or ion irradiation to form a two-dimensional pattern of a clean surface.~~

5. (Currently Amended) [[A]] The two-dimensional patterning method according to claim 3, further comprising:

after destroying and removing the blister together with the formed film,

~~wherein a two-dimensional pattern is formed by forming a film on a blister disposed on a substrate and destroying and removing the blister together with the formed film by electron irradiation or ion irradiation, and further by further forming a film on the surface from which the blister has been destroyed and removed with the use of difference in adsorption probability between the substrate surface protected by the blister and the surface not protected to form a two-dimensional pattern.~~

6. (Currently Amended) [[A]] The two-dimensional patterning method according to claim 4, further comprising:

after wherein a two-dimensional pattern is formed by executing surface reaction on a

~~blister disposed on a substrate and~~ destroying and removing the blister together with the reacted film, ~~by electron irradiation or ion irradiation, and further by executing chemical reaction on the surface from which the blister has been destroyed and removed with the use of difference in reactivity between the substrate surface protected by the blister and the surface not protected to form a two-dimensional pattern.~~

7. **(Previously Presented)** The two-dimensional patterning method according to claim 1, wherein the substrate is a silicon substrate or a metal substrate.

8. **(Previously Presented)** The two-dimensional patterning method according to claim 1, wherein the blister is formed by hydrogen ion irradiation, deuterium ion irradiation, or helium ion irradiation.

9. **(Currently amended)** The two-dimensional patterning method according to claim 1, wherein the blister ~~having~~ has a patterned configuration ~~and~~ is formed by ion irradiation through a mask.

10. **(Currently amended)** The two-dimensional patterning method according to claim 1, wherein the blister ~~having~~ has a patterned configuration ~~and~~ is formed by using focused ion beam.

11. **(Currently amended)** The two-dimensional patterning method according to claim [[2]]1, wherein the irradiation ion is any one of Ar<sup>+</sup>, Kr<sup>+</sup>, and Xe<sup>+</sup>.

12. **(Currently amended)** The two-dimensional patterning method according to claim 1, wherein the two-dimensional pattern is a two-dimensional pattern including a of an atomic species of a surface constituent atom of the substrate and a hetero atom.

13. **(Currently amended)** The two-dimensional patterning method according to claim 1, wherein the two-dimensional pattern is a pattern different in a pattern constructed by using a difference in film film formed in a lower layer than a surface layer structure between the substrate and the blister.

14. **(Currently amended)** The two-dimensional patterning method according to claim 1, wherein the two-dimensional pattern is an electric characteristic a pattern including film structures where electrical properties are different.

15. **(Currently amended)** The two-dimensional patterning method according to claim 1, wherein the two-dimensional pattern is a reactive pattern including film structures where reactive properties are different.

16. **(Currently amended)** The two-dimensional patterning method according to claim

15, wherein the two-dimensional pattern is ~~an affinity~~a pattern including film structures where affinities are different.

17. **(Currently amended)** The two-dimensional patterning method according to claim 16, wherein the two-dimensional pattern is pattern including a hydrophilic [[or]] surface and a hydrophobic pattern surface.

18. **(Previously Presented)** A manufacturing method of electronic device, wherein the two-dimensional patterning method according to claim 1 is employed.

19. **(Previously Presented)** A manufacturing method of magnetic device, wherein the two-dimensional patterning method according to claim 1 is employed.